FAIRCHILD

SEMICONDUCTOR

MPS6514

NPN General Purpose Amplifier

- This device is designed as a general purpose amplifier and switch.
- The useful dynamic range extends to 100mA as a switch and to 100MHz as an amplifier.



1. Emitter 2. Base 3. Collector

Absolute Maximum Ratings* Ta=25°C unless otherwise noted

Symbol	Parameter		Value	Units
CEO	Collector-Emitter Voltage		25	V
СВО	Collector-Base Voltage		40	V
ЕВО	Emitter-Base Voltage		4.0	V
)	Collector current	- Continuous	200	mA
J, T _{sta}	Junction and Storage Temperature		-55 ~ +150	°C

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

Electrical Characteristics T_a=25°C unless otherwise noted

Parameter	Test Condition	Min.	Max.	Units
eristics	÷			
Collector-Emitter Breakdown Voltage	$I_{\rm C} = 0.5 {\rm mA}, I_{\rm B} = 0$	25		V
Collector-Base Breakdown Voltage	$I_{\rm C} = 10 \mu A, I_{\rm E} = 0$	40		V
Emitter-Base Breakdown Voltage	$I_{\rm C} = 10\mu {\rm A}, I_{\rm C} = 0$	4.0		V
Collector Cutoff Current	$V_{CE} = 30V, I_E = 0$		50	nA
Collector Cutoff Current	$V_{CB} = 30V, I_E = 0, T = 100^{\circ}C$		1.0	μA
eristics *				
DC Current Gain	I _C = 2.0mA, V _{CE} = 10V	150	300	
	I _C = 100mA, V _{CE} = 10V	90		1
Collector-Emitter Saturation Voltage	I _C = 50mA, I _B = 5.0mA		0.5	V
I Characteristics				
Output Capacitance	$V_{CB} = 10V, I_F = 0, f = 100 \text{kHz}$		3.5	pF
	eristics Collector-Emitter Breakdown Voltage Collector-Base Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cutoff Current Collector Cutoff Current eristics * DC Current Gain Collector-Emitter Saturation Voltage I Characteristics	eristics I _C = 0.5mA, I _B = 0 Collector-Emitter Breakdown Voltage I _C = 10 μ A, I _E = 0 Emitter-Base Breakdown Voltage I _C = 10 μ A, I _E = 0 Emitter-Base Breakdown Voltage I _C = 10 μ A, I _C = 0 Collector Cutoff Current V _{CE} = 30V, I _E = 0 Collector Cutoff Current V _{CB} = 30V, I _E = 0, T = 100°C eristics * DC Current Gain I _C = 100mA, V _{CE} = 10V I _C = 100mA, V _{CE} = 10V ICollector-Emitter Saturation Voltage I _C = 50mA, I _B = 5.0mA	eristicsCollector-Emitter Breakdown Voltage $I_C = 0.5mA$, $I_B = 0$ 25Collector-Base Breakdown Voltage $I_C = 10\muA$, $I_E = 0$ 40Emitter-Base Breakdown Voltage $I_C = 10\muA$, $I_C = 0$ 4.0Collector Cutoff Current $V_{CE} = 30V$, $I_E = 0$ 4.0Collector Cutoff Current $V_{CB} = 30V$, $I_E = 0$ 50Collector Cutoff Current $V_{CB} = 30V$, $I_E = 0$, $T = 100^{\circ}C$ 4.0eristics *DC Current Gain $I_C = 2.0mA$, $V_{CE} = 10V$ 150 $I_C = 100mA$, $V_{CE} = 10V$ 9010Collector-Emitter Saturation Voltage $I_C = 50mA$, $I_B = 5.0mA$ 11Characteristics	eristicsCollector-Emitter Breakdown Voltage $I_C = 0.5mA$, $I_B = 0$ 25Collector-Base Breakdown Voltage $I_C = 10\muA$, $I_E = 0$ 40Emitter-Base Breakdown Voltage $I_C = 10\muA$, $I_C = 0$ 4.0Collector Cutoff Current $V_{CE} = 30V$, $I_E = 0$ 50Collector Cutoff Current $V_{CB} = 30V$, $I_E = 0$, $T = 100^{\circ}C$ 1.0eristics *DC Current Gain $I_C = 2.0mA$, $V_{CE} = 10V$ 150 $I_C = 100mA$, $V_{CE} = 10V$ 900.5I Characteristics

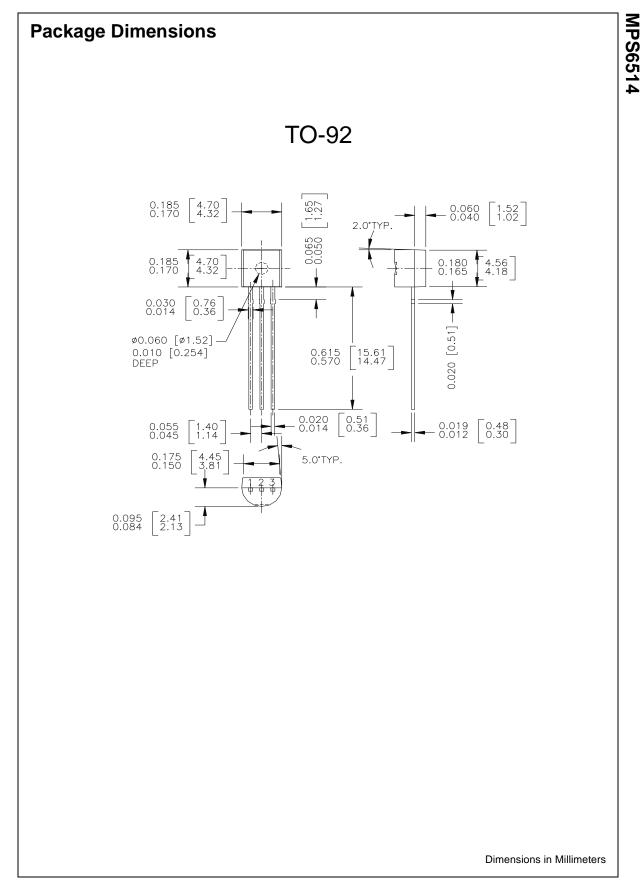
Pulse Test: Pulse Width $\leq 300 \mu s, \, Duty \, Cycle \leq 2.0\%$

Thermal Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Max.	Units
P _D	Total Device Dissipation	625	mW
-	Derate above 25°C	5.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

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Rev. A, May 2004

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